

Claims

1. A semiconductor device, comprising:

5 a stacked body including a first electrode layer, a second electrode layer provided to be electrically insulated from the first electrode layer in a stacking direction, and a third electrode layer provided to be electrically insulated from the second electrode layer in the stacking direction;

10 at least two first insulating layers provided in the stacked body to range from an upper end of the stacked body to a lower end of the stacked body, and extending in a first direction intersecting the stacking direction;

a first staircase portion provided in a first end region of the stacked body between the at least two first insulating layers;

15 a second staircase portion provided in a second end region of the stacked body located on a side opposite to the first end region between the at least two first insulating layers;

20 a second insulating layer extending in the first direction, and provided in the stacked body between the at least two first insulating layers, the second insulating layer dividing in a second direction the second electrode layer to a first portion and a second portion, the second insulating layer further dividing the third electrode layer in the second direction to a third portion and a fourth portion, the second direction crossing the first direction;

25 a first interconnection electrically connecting the first portion of the second electrode layer and the third portion of the third electrode layer; and

30 a second interconnection electrically connecting the second portion of the second electrode layer and the fourth portion of the third electrode layer, wherein

the first electrode layer is a word line,

the second electrode layer is a first selection gate layer, and
the third electrode layer is a second selection gate layer.

2. The device according to claim 1, wherein the word line is a
5 dummy word line.

3. The device according to claim 1, wherein
the stacked body includes a first column-shaped portion
provided in an intermediate region of the stacked body located
10 between the first end region and the second end region, the first
column-shaped portion extending in the stacking direction, and
the first column-shaped portion includes:
a semiconductor body extending in the stacking direction; and
a charge storage portion provided between the semiconductor body
15 and the first electrode layer.

4. The device according to claim 1, wherein
the first and second interconnections are provided in the
stacked body, and
20 the first and second interconnections are provided along the
second insulating layer.

~~5. The device according to claim 1, further comprising a third
insulating layer extending in the first direction, the third insulating
25 layer provided in the stacked body between the first insulating layer
and the second insulating layer, and dividing the second electrode
layer and the third electrode layer in the first direction.~~